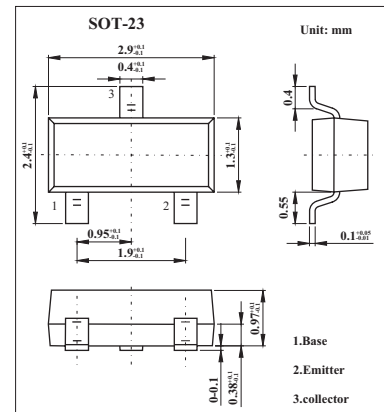


Silicon PNP Epitaxial Planar Type

2SA1022

■ Features

- High transition frequency f_T .
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CB0}	-30	V
Collector-emitter voltage (Base open)	V_{CEO}	-20	V
Emitter-base voltage (Collector open)	V_{EBO}	-5	V
Collector current	I_C	-30	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -10\text{ V}, I_E = 0$			-0.1	μA
	I_{CEO}	$V_{CE} = -20\text{ V}, I_B = 0$			-100	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -5.0\text{ V}, I_C = 0$			-10	μA
Forward current transfer ratio	h_{FE}	$V_{CE} = -10\text{ V}, I_C = -1\text{ mA}$	70		220	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10\text{ mA}, I_B = -1\text{ mA}$		-0.1		V
Base to emitter voltage	V_{BE}	$V_{CE} = -10\text{ V}, I_C = -1\text{ mA}$		-0.7		V
Transition frequency	f_T	$V_{CB} = -10\text{ V}, I_E = 1\text{ mA}, f = 200\text{ MHz}$	150	300		MHz
Noise figure	NF	$V_{CB} = -10\text{ V}, I_E = 1\text{ mA}, f = 5\text{ MHz}$		2.8		dB
Reverse transfer impedance	Z_{rb}	$V_{CB} = -10\text{ V}, I_E = 1\text{ mA}, f = 2\text{ MHz}$		22		Ω
Common emitter reverse transfer capacitance	C_{re}	$V_{CE} = -10\text{ V}, I_C = -1\text{ mA}, f = 10.7\text{ MHz}$		1.2		pF

■ h_{FE} Classification

Marking	EB	EC
h_{FE}	70~140	110~220